# 2SB561

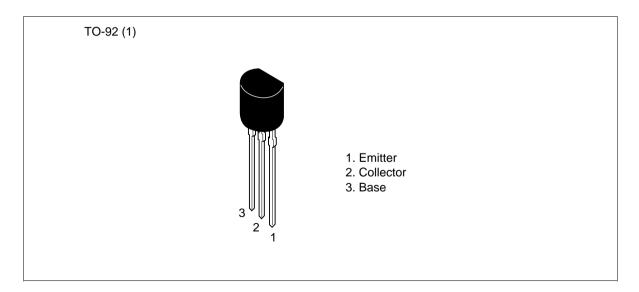
## Silicon PNP Epitaxial

# **HITACHI**

#### **Application**

- Low frequency power amplifier
- Complementary pair with 2SD467

#### Outline





## 2SB561

## **Absolute Maximum Ratings** (Ta = 25°C)

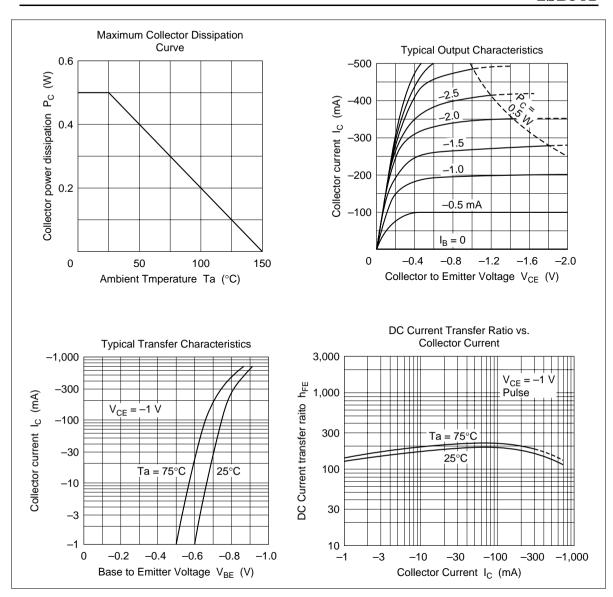
Item	Symbol	Ratings	Unit
Collector to base voltage	$V_{\text{CBO}}$	<b>–</b> 25	V
Collector to emitter voltage	V <sub>CEO</sub>	-20	V
Emitter to base voltage	$V_{EBO}$	<b>–</b> 5	V
Collector current	I <sub>c</sub>	-0.7	A
Collector peak current	i <sub>C(peak)</sub>	-1.0	A
Collector power dissipation	P <sub>c</sub>	0.5	W
Junction temperature	Tj	150	°C
Storage temperature	Tstg	-55 to +150	°C

#### **Electrical Characteristics** ( $Ta = 25^{\circ}C$ )

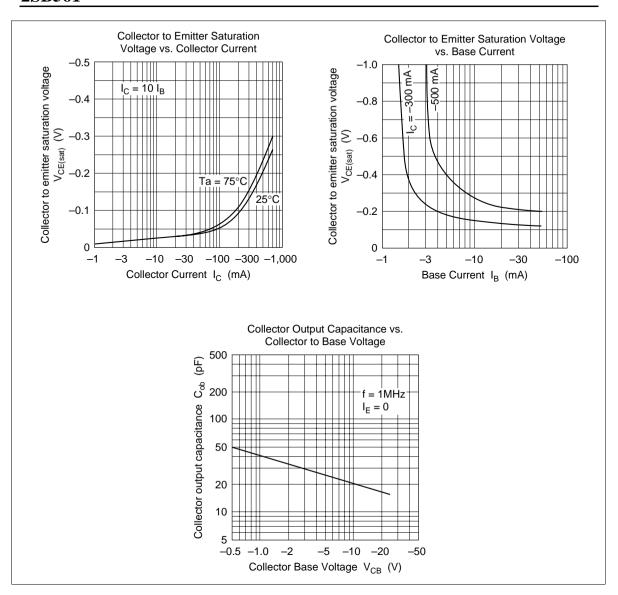
Item	Symbol	Min	Тур	Max	Unit	Test conditions
Collector to base breakdown voltage	$V_{\text{(BR)CBO}}$	-25	_	_	V	$I_{c} = -10 \ \mu\text{A}, \ I_{E} = 0$
Collector to emitter breakdown voltage	$V_{(BR)CEO}$	-20	_	_	V	$I_{C} = -1 \text{ mA}, R_{BE} = \infty$
Emitter to base breakdown voltage	$V_{(BR)EBO}$	<b>-</b> 5	_	_	V	$I_{E} = -10 \mu\text{A}, \ I_{C} = 0$
Collector cutoff current	I <sub>CBO</sub>	_	_	-1.0	μΑ	$V_{CB} = -20 \text{ V}, I_{E} = 0$
DC current transfer ratio	h <sub>FE</sub> *1	85	_	240		$V_{CE} = -1 \text{ V},$ $I_{C} = -0.15 \text{ A (Pulse test)}$
Collector to emitter saturation voltage	V <sub>CE(sat)</sub>	_	-0.2	-0.5	V	$I_{\rm C} = -0.5 \text{ A}, I_{\rm B} = -0.05 \text{ A}$
Base to emitter voltage	$V_{BE}$	_	-0.75	-1.0	V	$V_{CE} = -1 \text{ V}, I_{C} = -0.15 \text{ A}$
Gain bandwidth product	f <sub>T</sub>	_	350	_	MHz	$V_{CE} = -1 \text{ V}, I_{C} = -0.15 \text{ A}$
Collector output capacitance	Cob	_	20	_	pF	$V_{CB} = -10 \text{ V}, I_{E} = 0$ f = 1 MHz

Note: 1. The 2SB561 is grouped by  $h_{FE}$  as follows.

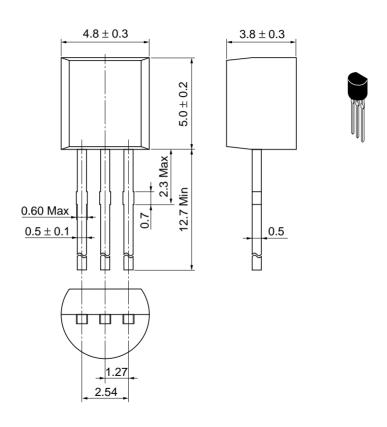
B C 85 to 170 120 to 240



## 2SB561



Unit: mm



Hitachi Code	TO-92 (1)
JEDEC	Conforms
EIAJ	Conforms
Weight (reference value)	0.25 g

#### **Cautions**

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